



JMP(C.E.F)13N65B

Description

JMP N-channel MOSFET

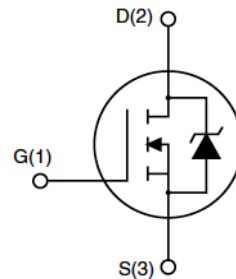
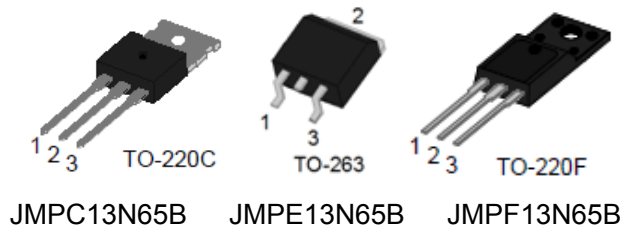
Features

- 650V,13A
- $R_{DS(ON)} = 0.65\Omega$ (Typ.) @ $V_{GS} = 10V, I_D = 6.5A$
- Fast Switching
- Improved dv/dt Capability
- 100% Avalanche Tested

Application

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS)
- Power Factor Correction (PFC)

Package



Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Max.		Units	
		TO-220C/TO-263	TO-220F		
V_{DSS}	Drain-Source Voltage	650		V	
V_{GSS}	Gate-Source Voltage	± 30		V	
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	13	A	
		$T_C = 100^\circ\text{C}$	8	A	
I_{DM}	Pulsed Drain Current ^{note1}	52		A	
E_{AS}	Single Pulsed Avalanche Energy ^{note2}	562		mJ	
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	147	65	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		0.85	1.92	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		60	62.5	$^\circ\text{C}/\text{W}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$	



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Electrical Characteristics (T_C=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	650	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650V, V _{GS} = 0V, T _J = 25°C	-	-	1	μA
		V _{DS} = 520V, V _{GS} = 0V, T _J = 125°C	-	-	100	
I _{GSS}	Gate to Body Leakage Current	V _{DS} = 0V, V _{GS} = ±30V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.0	-	4.0	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} = 10V, I _D = 6.5A	-	0.65	0.8	Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	-	1264	-	pF
C _{oss}	Output Capacitance		-	149	-	pF
C _{rss}	Reverse Transfer Capacitance		-	18	-	pF
Q _g	Total Gate Charge	V _{DD} = 520V, I _D = 13A, V _{GS} = 10V	-	35	-	nC
Q _{gs}	Gate-Source Charge		-	7	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	18	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = 325V, I _D = 13A, R _G = 25Ω	-	23	-	ns
t _r	Turn-on Rise Time		-	15	-	ns
t _{d(off)}	Turn-off Delay Time		-	90	-	ns
t _f	Turn-off Fall Time		-	30	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	13	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	52	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _{SD} = 13A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 13A, di/dt = 100A/μs	-	320	-	ns
Q _{rr}	Reverse Recovery Charge		-	4.2	-	μC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. I_{AS} = 7.5A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C

3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 1%



Typical Performance Characteristics

Figure 1: Output Characteristics

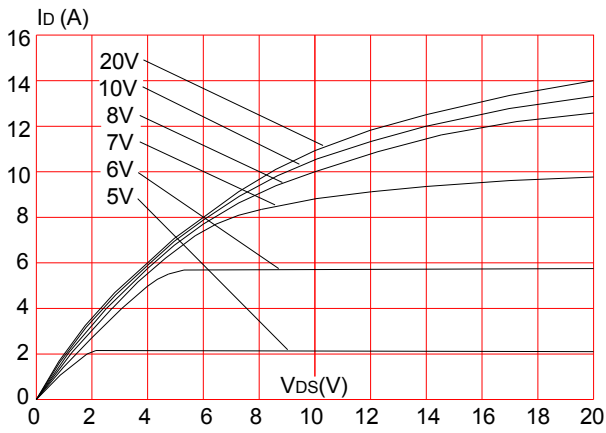


Figure 2: Typical Transfer Characteristics

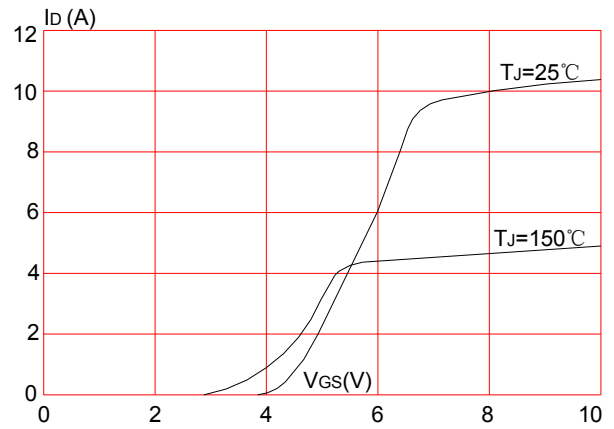


Figure 3: On-resistance vs. Drain Current

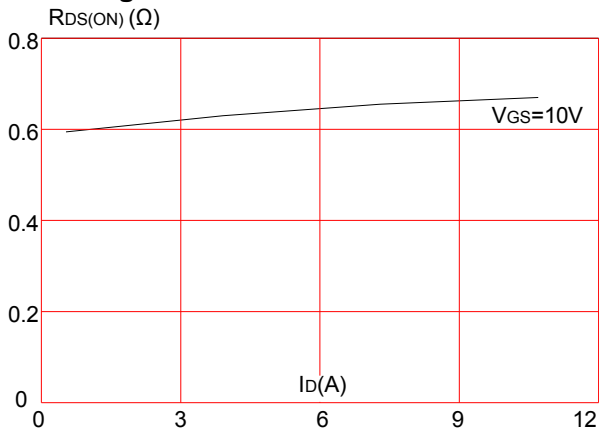


Figure 4: Body Diode Characteristics

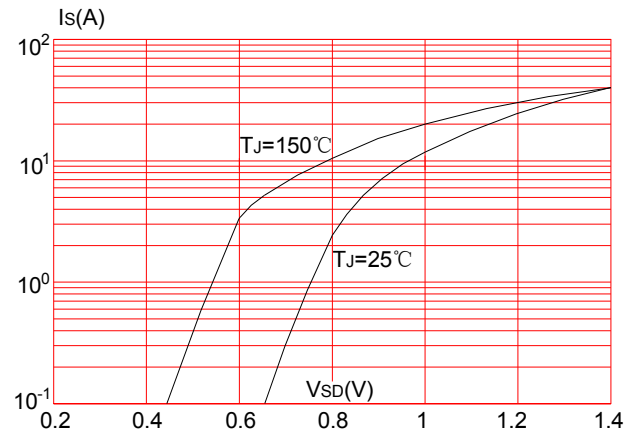


Figure 5: Gate Charge Characteristics

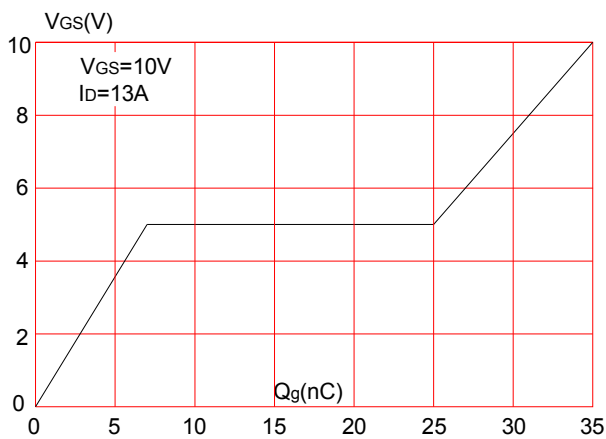
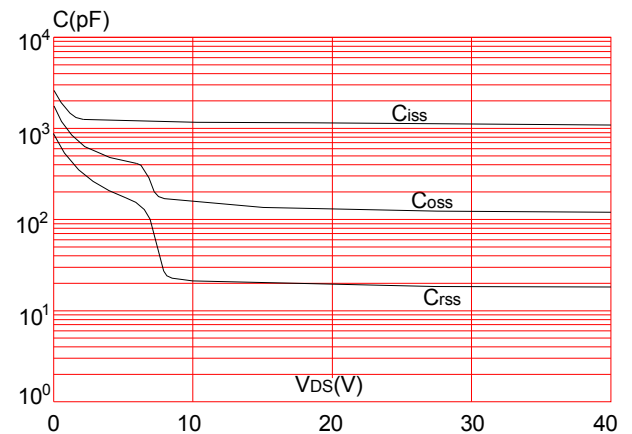


Figure 6: Capacitance Characteristics





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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

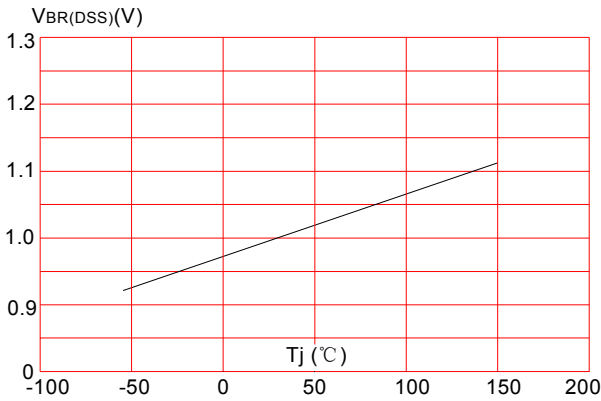


Figure 8: Normalized on Resistance vs. Junction Temperature

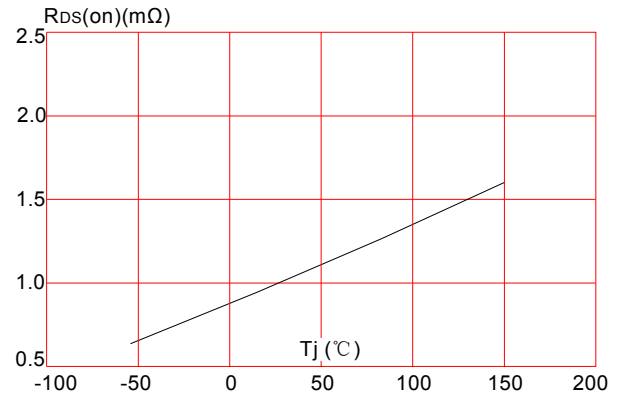


Figure 9: Maximum Safe Operating Area

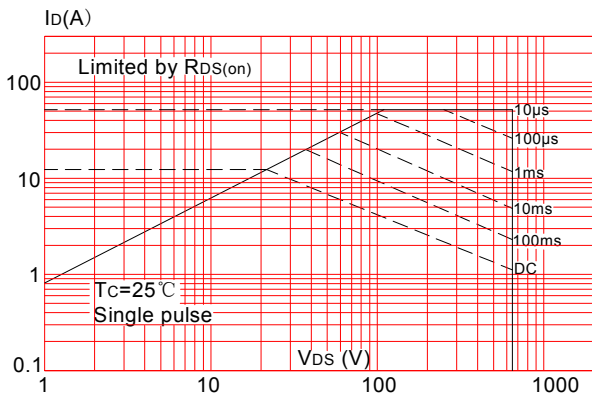


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

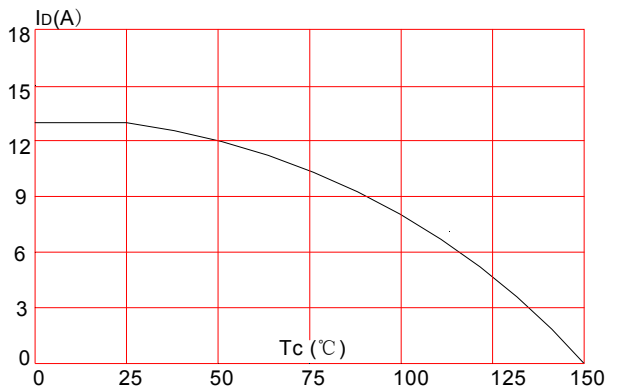


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220C,TO-263)

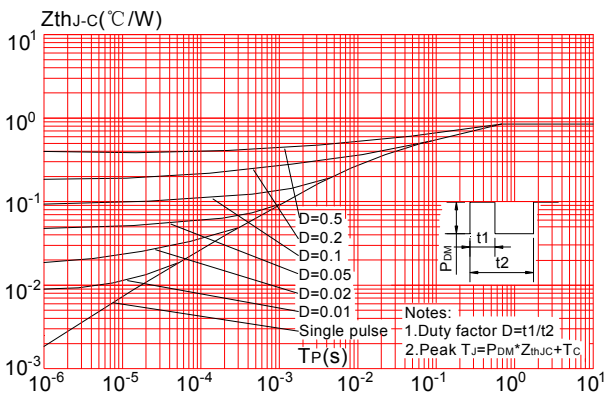
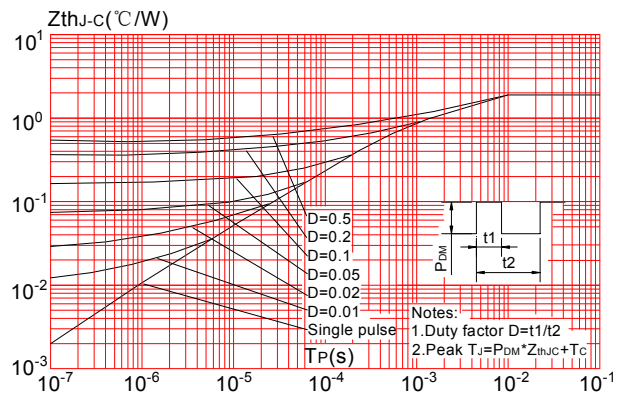


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220F)



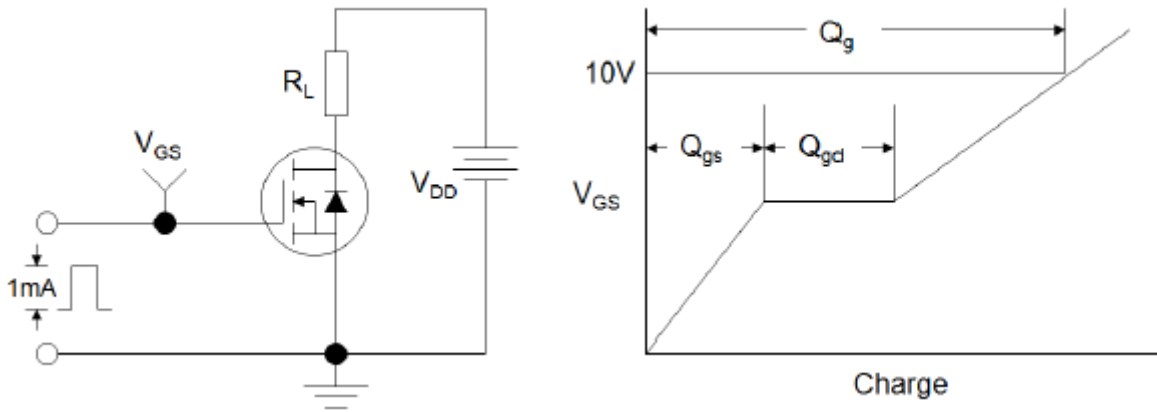


Figure1:Gate Charge Test Circuit & Waveform

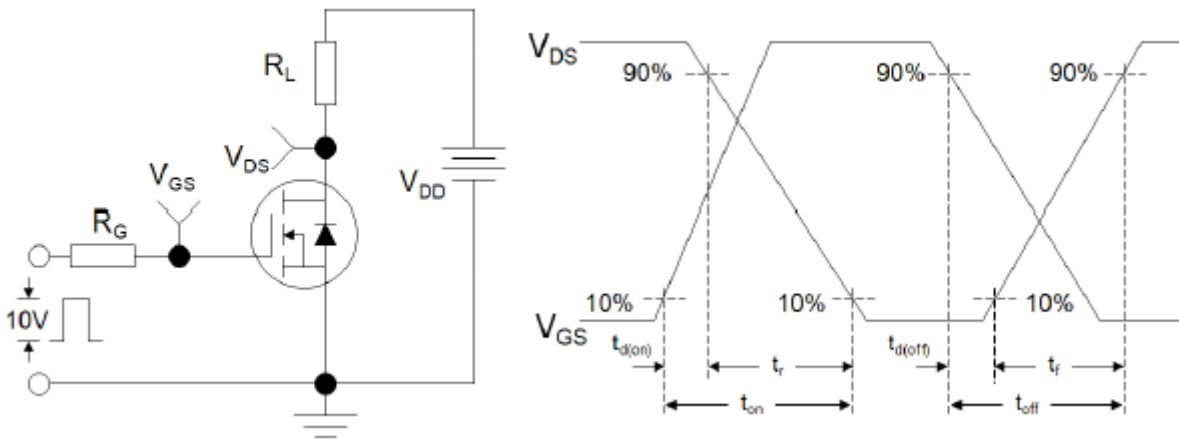


Figure 2: Resistive Switching Test Circuit & Waveforms

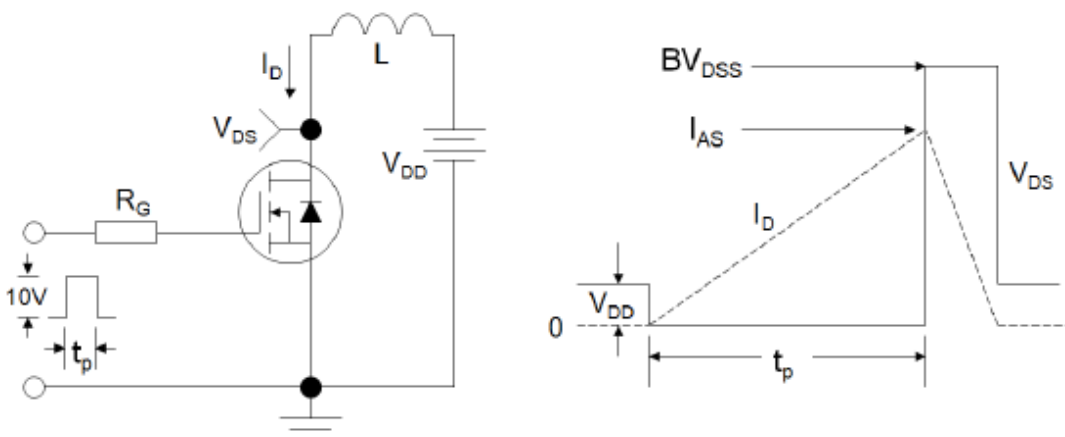


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

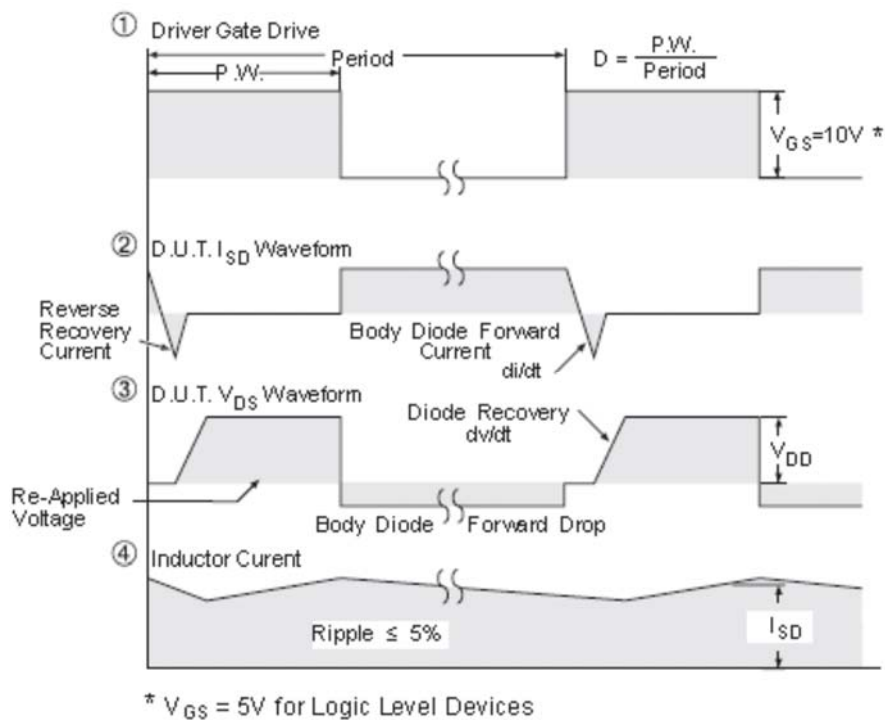
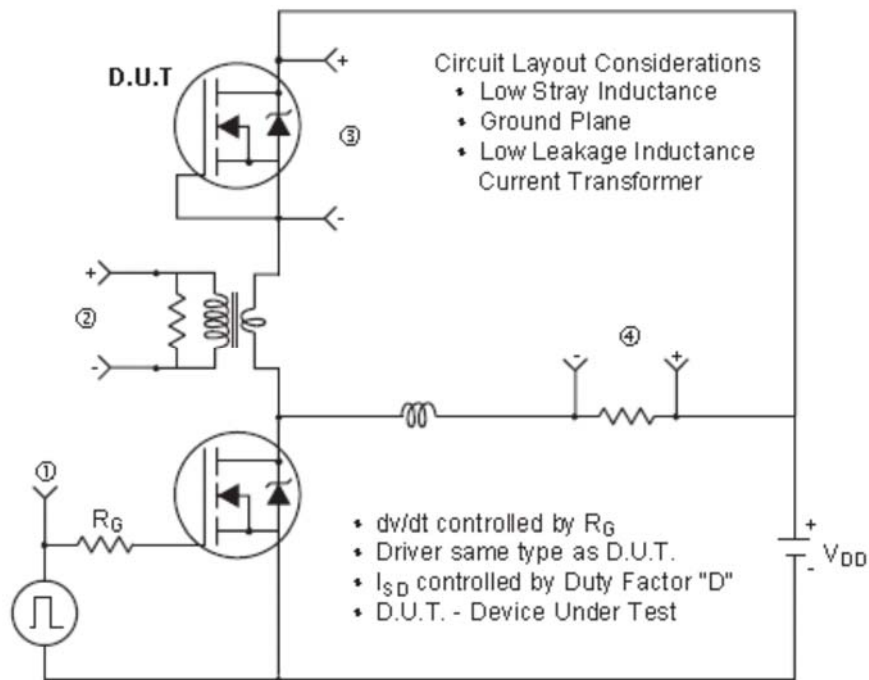
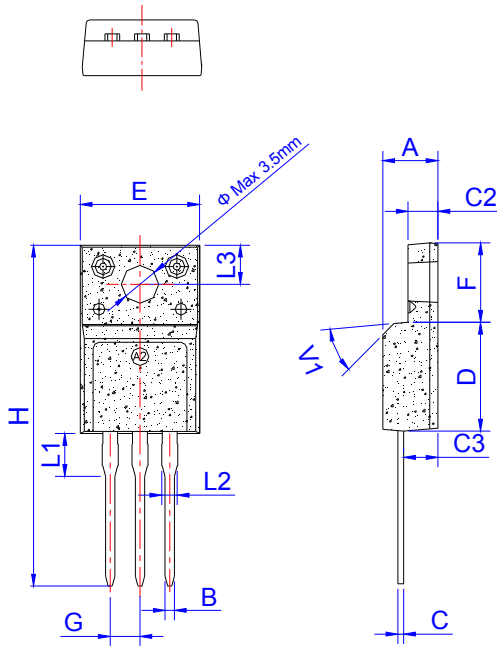


Figure 4: Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)



Package Mechanical Data



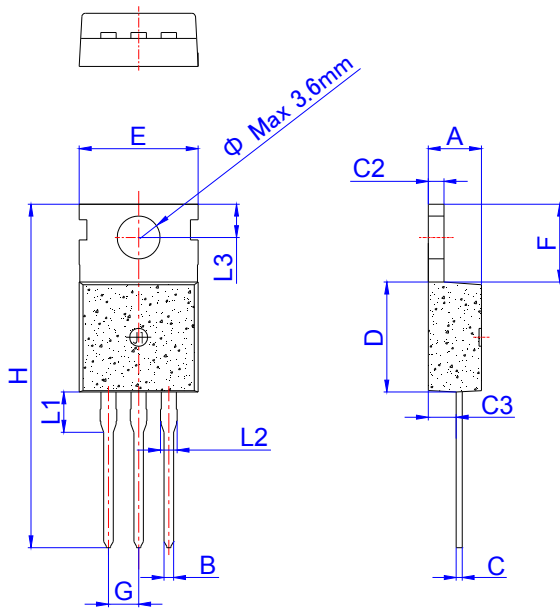
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

Package Information -TO-220F

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	50	1,000	8,000



Package Mechanical Data



TO-220C

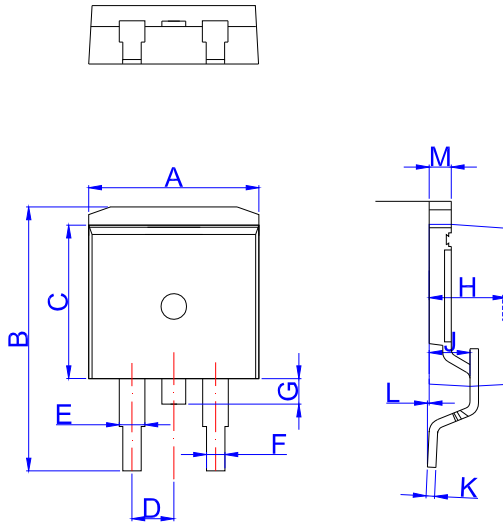
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		1.181
B	0.70		0.90	0.027		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.086		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	11.0		11.7
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	

Package Information -TO-220C

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	50	1,000	8,000



Package Mechanical Data



TO-263

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053

Package Information -TO-263

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	50	1,000	8,000

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